

**MIL PROCESSING TEST PLAN FOR DLZ SERIES – H1 VERSIONS  
(Unidirectional)**

TEST	CONDITION	MIL-STD-750 TEST METHOD
<b>Internal Visual</b>		2072
<b>Storage</b>	T <sub>A</sub> = +150°C for 24 hours	1032
<b>Temp Cycle</b>	10 cycles, 15 minutes each extreme @ min/max rated temps	1051
<b>Acceleration</b>	20KG, Y1 axis, no hold time	2006
<b>Electrical</b>	Reverse Current (I <sub>R</sub> ) @ rated V <sub>WM</sub> Breakdown Voltage (V <sub>(BR)</sub> ) @ I <sub>T</sub>	4016 4022
<b>Pulse</b>	20 pulses @ I <sub>pp</sub> = 10A, t <sub>p</sub> = 8 x 20μs	
<b>Electrical</b>	Reverse Current (I <sub>R</sub> ) @ rated V <sub>WM</sub>	4016
<b>Burn-in(HTRB)</b>	T <sub>A</sub> = +125°C @ rated V <sub>WM</sub> for 160 hours	1038
<b>Electrical</b>	Reverse Current (I <sub>R</sub> ) @ rated V <sub>WM</sub> , D-I <sub>R</sub> = 100% or 20% of Group A limit, whichever is greater Breakdown Voltage (V <sub>(BR)</sub> ) @ I <sub>T</sub> , D-V <sub>(BR)</sub> ±2% from initial reading	4016 4022
<b>Fine Leak</b>	1 x 10 <sup>-8</sup> atmcc/sec	1071G/H
<b>Gross Leak</b>	T <sub>A</sub> = +125°C, no bubbles	1071C/D
<b>Marking</b>		
<b>Group A</b>	Reverse Current (I <sub>R</sub> ) @ rated V <sub>WM</sub> Breakdown Voltage (V <sub>(BR)</sub> ) @ I <sub>T</sub> Clamping Voltage (V <sub>C</sub> ) @ I <sub>pp</sub> , t <sub>p</sub> = 8 x 20μs Capacitance @ 0V	4016 4022 4001